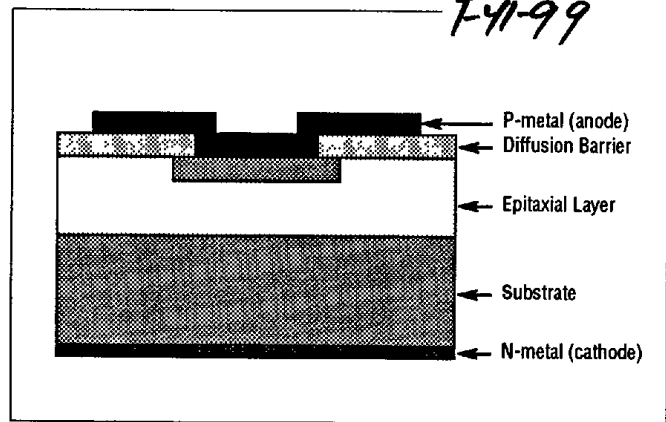
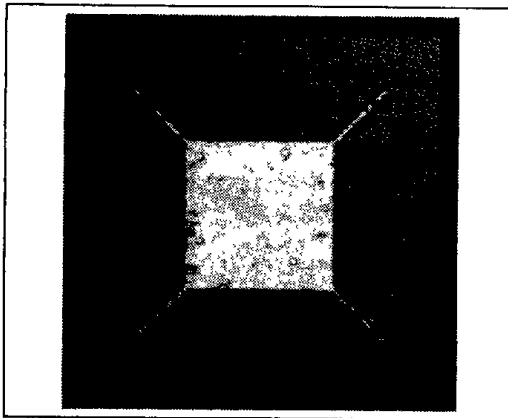


**SIEMENS**

**RP-12C  
Mask-Diffused GaAsP LED**

**PART NO. 2680-7075**

Custom  
Optoelectronic  
Products



**DESCRIPTION**

Siemens RP-12C is a mask-diffused GaAsP light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for lamp and display applications.

**MATERIAL**

Epitaxial Layer: GaAs<sub>1-x</sub>P<sub>x</sub> : Te  
 Substrate: GaAs : Si or GaAs : Te  
 Metalizations: Anode Aluminum  
 Cathode Gold-Germanium

**Dimensions**

(center to center): Height 0.012"  
 Width 0.012"  
 Thickness 0.010"

**TYPICAL DEVICE PARAMETERS**

Forward I-V Characteristics	$V_{F3}$	1.70 V	@ 20 mA
	$V_{F2}$	1.64 V	@ 10 mA
	$V_{F1}$	1.45 V	@ 100 $\mu$ A
Reverse I-V Characteristics	$V_{R1}$	-25.0 V	@ -10 $\mu$ A
Peak EL Wavelength	$\lambda$	655 nm	@ 20 mA
Spectral Half-Width	FWHM	40 nm	@ 20 mA
Luminous Intensity	LI	500 $\mu$ Cd	@ 10 mA